



IRF2805LPBF Information

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For Reference Only

Part Number IRF2805LPBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 55V 135A TO-262

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF2805LPBF Specifications

Manufacturer Part Number IRF2805LPBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 135A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 230nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5110pF @ 25V Vgs (Max) ±0V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 4.7 mOhm @ 104A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) S5V Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 110pt Capacitance (Ciss) (Max) @ Vds 1110pf @ 25V Vgs (Max) 120v FET Feature - Power Dissipation (Max) Avgs (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 4.7 mOhm @ 104A, 10V Operating Temperature - Supplier Device Package TO-262 Package / Case TO-262 Package / Case TO-262AA	Manufacturer Part Number	IRF2805LPBF
Package TO-262-3 Long Leads, 12Pak, TO-262AA Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 135A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 230nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5110pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 4.7 mOhm @ 104A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262-3 Long Leads, I2Pak, TO-262AA	Manufacturer	Infineon Technologies
Package TO-262-3 Long Leads, I2Pak, TO-262AA Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 135A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 110pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.7 mOhm @ 104A, 10V Operating Temperature Supplier Device Package TO-262-3 Long Leads, I2Pak, TO-262AA	Category	Discrete Semiconductor Products
SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C135A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs230nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5110pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs4.7 mOhm @ 104A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA		Transistors - FETs, MOSFETs - Single
FET Type N-Channel MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.7 mOhm @ 104A, 10V Operating Temperature Supplier Device Package Package / Case N-Channel N-Chanle N-Channel N-Channel N-Channel N-Channel N-Channel N-Chanle N-Channel N-Channel N-Channel N-Channel N-Chanle N-Chanle N-Channel N-Chanle N-Chanle N-Chanle N-Chanle N-Chanle N-Channel N-Chanle N-Chanle	Package	TO-262-3 Long Leads, I2Pak, TO-262AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C135A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs230nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5110pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs4.7 mOhm @ 104A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Series	HEXFET?
Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C135A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs230nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5110pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs4.7 mOhm @ 104A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1350 (230nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.7 mOhm @ 104A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case 135A (Tc) 10V 4V @ 250μA 230nC @ 10V 5110pF @ 25V 240V 5110pF @ 25V 70-262-3 Long Leads, 12Pak, TO-262AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs230nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5110pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs4.7 mOhm @ 104A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	Drain to Source Voltage (Vdss)	55V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) At 7 mOhm @ 104A, 10V Operating Temperature Supplier Device Package Package / Case 4V @ 250μA 230nC @ 10V 5110pF @ 25V 5110	Current - Continuous Drain (Id) @ 25°C	135A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 5110pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.7 mOhm @ 104A, 10V Operating Temperature Operating Temperature Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.7 mOhm @ 104A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs4.7 mOhm @ 104A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	Gate Charge (Qg) (Max) @ Vgs	230nC @ 10V
FET Feature - Consider the Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 4.7 mOhm @ 104A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Input Capacitance (Ciss) (Max) @ Vds	5110pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.7 mOhm @ 104A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs4.7 mOhm @ 104A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Power Dissipation (Max)	200W (Tc)
Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Rds On (Max) @ Id, Vgs	4.7 mOhm @ 104A, 10V
Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Mounting Type	Through Hole
	Supplier Device Package	TO-262
Report errors?	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
		Report errors?

IRF2805LPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF2805LPBF Payment Methods



















IRF2805LPBF Shipping Methods













If you have any question about IRF2805LPBF, please do not hesitate to contact us!

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